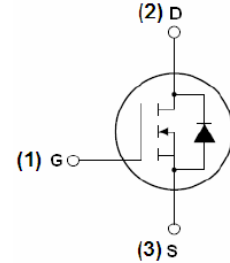


N-Channel PowerMOSFET Wafer Datasheet

FEATURES

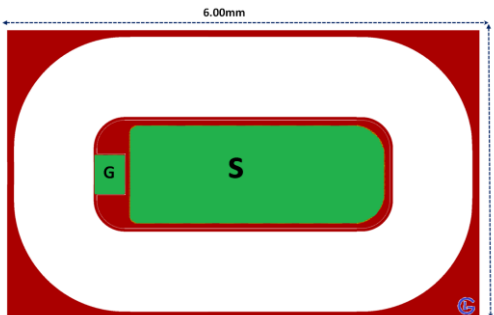
- 2500V、0.5A*, N-channel
- $R_{DS(on)}=200.0\Omega(\text{MAX})$
- Ultra low Q_{gd}
- Fast switching



Electrical Characteristics($T_J=25^\circ\text{C}$)

Parameter	Description	Min.	Typ.	Max.	Unit	Test Condition
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	2500			V	$V_{GS}=0V, I_D=-250\mu A$
$R_{DS(on)1}$	Static Drain-Source On-Resistance			200.0	Ω	$V_{GS}=10V, I_D=0.25A$
$V_{GS(th)}$	Gate Threshold Voltage	2.5		4.5	V	$V_{DS}=V_{GS}, I_D=-250\mu A$
I_{DSS}	Drain-to-Source Leakage Current			10	μA	$V_{DS}=2500V, V_{GS}=0V, T_J=25^\circ\text{C}$
I_{GSS}	Gate-Body Leakage Current			± 100	nA	$V_{GS}=\pm 30V$
V_{SD}	Body Diode Voltage			2.0	V	$V_{GS}=0V, I_{SD}=0.5A$
T_J, T_{stg}	Operating and Storage Temperature Range	-55~+150			$^\circ\text{C}$	

Mechanical Data

Die Size	6000×3750	μm^2	
Gate Pad Size	380×480		
Source Pad Size	No Passivation		
Scribe Line Size	80	μm	
Wafer Diameter	150	mm	
Wafer Thickness	400	μm	
Passivation Frontside	No	---	
Source Metallization	AL	4.0	
Drain Metallization	Ti- Ni - Ag	1.3	
Reject Ink Dot Size	0.51	mm	
Recommended Storage Environment	Store in original container, in dessicated nitrogen, with no contamination		

* Electrical characteristics are reported for the reference packaged part (TO-220) and can not be guaranteed in die sales form.

Variations in customer packaging materials, dimensions and processes may affect parametric performance.